Status and Outlook of Si-Strip-Sensors from Infineon Technologies AG Hacker Johannes, 2017-12-11 11th International "Hiroshima" Symposium on the **Development and Application of Semiconductor Tracking Detectors (HSTD11)**







CERN LHC ATLAS + CMS Phase-II Upgrades

Long Shutdown 3 (LS3) scheduled for 2024-2025

- Accelerator upgrade to High-Luminosity-(HL)-LHC
- Upgrade of experiments necessary
 - Existing systems reach end of life (radiation damage)
 - − Increase in luminosity at HL-LHC: 300 \rightarrow 3000 fb⁻¹

Phase-II Upgrade of ATLAS + CMS:

- Complete exchange of Outer Trackers
 → ~200 m² Si Sensors/experiment needed
- CMS: New Highly Granularity Calorimeter (HGCal)
 → 600 m² Si Sensors (8 inch)

Both experiments need industrial parners

- Industrial production necessary due to large quantities
- → Cooperation HEPHY/Vienna & Infineon Technologies





- HEPHY Vienna and Infineon Technologies cooperate since 2009 on the development of Si-sensors for HL-LHC-experiments
- Responsibilities
 - HEPHY: Layout-design, characterization, test-beams, irradiations, device-simulations
 - Infineon: Process-engineering, processing, establish series testing at Infineon
- > Focus
 - Single sided planar AC-coupled n-in-p Si-strip sensors for Trackers of ATLAS + CMS Phase II Upgrades in 6"-technology Active thicknesses: 300/320 um and 240 um
 - Single sided planar DC-coupled n-in-p Si-pad sensors for HGC of CMS Phase II Upgrade in 8"-technology, 300, 200, 120 um
- Following measurements were done by HEPHY/Vienna if not stated otherwise



Achievements Overview

Wafer size	Polarity	Layout	Chipsize [cm ²] main sensor	Thickness [µm] physical ≈ active
6"	p-in-n FZ	AC-Strip	10 x 7	200, 300
8"	n-in-p FZ	AC-Strip	15 x 10	200, 300
8"	n-in-p FZ	DC-Pad	18 x 16 hexagonal	140, 200, 300, 350
6"	n-in-p FZ	AC-Strip	5 x 10	240, 500

2012













World's first AC-coupled Sensors on 8" Wafers

- > Wafer for CMS-Phase II-Upgrade-Strip-Tracker
 - Wafer diameter (8" wafer): 200 mm
 - Resistivity 3..8 kΩcm, n-on-p float zone, orientation <100>
 - 200 µm and 300 µm physical thickness
- > Main Sensor
 - Size: 94.183 x 153.4 mm²
 - Strips: 2032, Strip length: 75.6 mm
 - Strip Pitch: 90 µm, P-stop: Atoll
- > Split groups for runs:
 - p-stop / p-spray, Dose, Profile
 - Different R_poly doping



100.0n

80.0n

60.0n

40.0n

20.0n

0.0

Current (A)

AC-coupled Strip-Sensors on 8" Wafers Global parameters IV and CV

- Sensor-size: 15 cm x 9 cm >
- Full depletion voltage of \sim 75 V >
- Sensor-HV-stability to be improved >

IV Diodes

Voltage (V)

Diodes are HV-stable >

03

<u>05</u>

06

07

08

10

11

12

14

<u>17</u>

18

<u>20</u>

21

<u>24</u> *





IV 2S-sensor

5μ



Wafer No.

6

AC-coupled Strip-Sensors on 8" Wafers Strip parameters of 9 2S_long sensors





Strip Coupling Capacitance



Polysilicon Resistance



Current Through the Strip Dielectric



> All strip-parameters of target-process "Std_BS" are in spec.

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AC-coupled Strip-Sensors on 8" Wafers Irradiation



- > Proton + Neutron irradiations of sensors and diodes were performed
- Difference in current before and after irradiation divided by the active volume after annealing of 10 min at 60 °C vs the 1 MeV neutron equivalent fluence, measured at -20 °C, scaled to 20 °C



- > α -value: (5.27±0.23)·10⁻¹⁷ A/cm in line with theoretical expectations
- Radiation hardness of sensors of Infineon validated

8

AC-coupled Strip-Sensors on 8" Wafers Beam-Test: Most Probable Value (infineon

 Electron beam test conducted at DESY using a ALiBaVa Readout System

Unirradiated sensor



Irradiated sensor with neutrons 3.5.10¹⁴ n_{eq} cm⁻² @ TRIGA/JSI



AC-coupled Strip-Sensors on 8" Wafers Beam-Test: Charge collection efficiency

ncy Baby module



Irradiated sensor with neutrons $3.5 \cdot 10^{14} n_{eq} \text{ cm}^{-2}$ @ TRIGA/JSI



Summary Beam-Test-Results: Sensors perform very well



Infineon



CMS High Granularity Calorimeter

- > CMS will upgrade it's forward calorimeter
- > Si-sensors+Scintilators
- > 600 m² Si-sensors
- > 8" technology baseline
- Active thicknesses
 - 300, 200, 120 um
- > 183 connected hexagonal diodes/pads
 - No common biasing (no bias ring)
 - Each pad is basically an individual diode
 - Biasing through the readout chip in module
 - For testing all pads have to be biased as well Pad
 - This complicates sensor testing







CMS High Granularity Calorimeter 8" planar n-in-p technology



 World's first 8"-HGC-wafers were produced and characterized



- High voltage-stability needs to be improved
- New processing-concept is currently in processing



CMS-Tracker PS-Sensors 2017



- > New design with CMS-Tracker "PS"-Sensor 5 cm x 10 cm
- > 500 um active~phyiscal thickness by intention for development



- Smaller Sensor & Diodes stable up to more than 1500 V
- Larger Sensors: HV-stability-improvement is ongoing



Summary and Conclusions

- Processes for both 6" and 8" planar n-in-p strip & pad-sensors are created and characterized
- > Strip parameters are in spec
- Radiation hardness is demonstrated
- > Beam-Test: very good performance
- > HV-stability needs to be improved
 - Infineon is working on solving this issue
- > Thanks for the work by HEPHY/Vienna
 - T. Bergauer, M. Dragicevic, A. König, E. Pree V. Hinger, D. Blöch, M. Valentan

Thanks for your attention!





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